

and expense to Applicants and duplicative examination by the Patent Office. Thus, withdrawal of the Restriction Requirement is respectfully requested.

AMENDMENT AFTER FINAL REJECTION UNDER 37 CFR §1.116

In reply to the January 8 Office Action, please amend the above-identified application as follows:

IN THE CLAIMS:

Please replace claims 1 and 14 as follows:

1. (Thrice Amended) A method of manufacturing a thin-film transistor, comprising:

forming a channel region facing a gate electrode through a gate insulating film;

forming source and drain regions connected to the channel region in a semiconductor film that is formed on a surface of an insulating substrate; and

forming a recombination center by introducing an impurity into the channel region so that a distance between the recombination center and the drain region is shorter than a distance between the recombination center and the source region,

wherein the recombination center is detached from the drain region.

14. (Twice Amended) A method of manufacturing a display device comprising a thin-film transistor that is manufactured by:

forming a channel region facing a gate electrode through a gate insulating film;

forming source and drain regions connected to the channel region in a semiconductor film that is formed on a surface of an insulating substrate; and

forming a recombination center that captures carriers in the channel region by introducing an impurity into said channel region so that a distance between the recombination